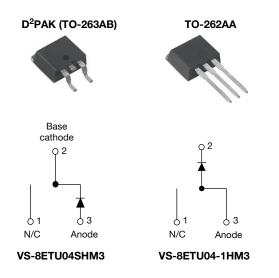


Vishay Semiconductors

Ultrafast Rectifier, 8 A FRED Pt®



| PRIMARY CHARACTERISTICS | | | | | | | | |
|----------------------------------|---|--|--|--|--|--|--|--|
| I _{F(AV)} | 8 A | | | | | | | |
| V _R | 400 V | | | | | | | |
| V _F at I _F | 0.94 V | | | | | | | |
| t _{rr} typ. | 35 ns | | | | | | | |
| T _J max. | 175 °C | | | | | | | |
| Package | D ² PAK (TO-263AB), TO-262AA | | | | | | | |
| Circuit configuration | Single | | | | | | | |

FEATURES

- Ultrafast recovery time
- Low forward voltage drop
- Low leakage current
- 175 °C operating junction temperature
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C



FREE

- AEC-Q101 qualified, meets JESD 201, class 1
 whisker test
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

Vishay Semiconductors FRED Pt[®] series are the state of the art ultrafast recovery rectifiers specifically designed with optimized performance of forward voltage drop and ultrafast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

| ABSOLUTE MAXIMUM RATINGS | | | | | | | | | | |
|---|-----------------------------------|-------------------------|-------------|-------|--|--|--|--|--|--|
| PARAMETER | SYMBOL | TEST CONDITIONS | MAX. | UNITS | | | | | | |
| Repetitive peak reverse voltage | V _{RRM} | | 400 | V | | | | | | |
| Average rectified forward current | I _{F(AV)} | T _C = 155 °C | 8 | | | | | | | |
| Non-repetitive peak surge current | I _{FSM} | T _C = 25 °C | 100 | А | | | | | | |
| Repetitive peak forward current | I _{FRM} | | 16 | | | | | | | |
| Operating junction and storage temperatures | T _J , T _{Stg} | | -55 to +175 | °C | | | | | | |

| ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified) | | | | | | | | | | |
|--|-------------------------------------|---|------|------|------|-------|--|--|--|--|
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNITS | | | | |
| Breakdown voltage, blocking voltage | V _{BR} , V _R | I _R = 100 μA | 400 | - | - | | | | | |
| Forward voltage | VF | I _F = 8 A | - | 1.19 | 1.3 | V | | | | |
| | ۷F | I _F = 8 A, T _J = 150 °C | - | 0.94 | 1.0 | | | | | |
| | I _R | $V_R = V_R$ rated | - | 0.2 | 10 | | | | | |
| Reverse leakage current | | $T_J = 150 \ ^{\circ}C, \ V_R = V_R \ rated$ | - | 20 | 500 | μΑ | | | | |
| Junction capacitance | CT | V _R = 400 V | - | 14 | - | pF | | | | |
| Series inductance | L _S | Measured lead to lead 5 mm from package body | - | 8.0 | - | nH | | | | |

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Document Number: 95841

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| DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25 \text{ °C}$ unless otherwise specified) | | | | | | | | | | |
|---|------------------|---|--|------|------|------|-------|--|--|--|
| PARAMETER | SYMBOL | TEST CO | NDITIONS | MIN. | TYP. | MAX. | UNITS | | | |
| | | I _F = 1.0 A, dI _F /dt = | $I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 50 \text{ A}/\mu\text{s}, V_R = 30 \text{ V}$ | | | 60 | | | | |
| Reverse recovery time | t _{rr} | T _J = 25 °C | | - | 43 | - | ns | | | |
| | | T _J = 125 °C | | - | 67 | - | | | | |
| Deals recovery current | I _{RRM} | T _J = 25 °C | $I_F = 8 A$ | - | 2.8 | - | A | | | |
| Peak recovery current | | T _J = 125 °C | dl _F /dt = 200 A/µs V _R = 200 V | - | 6.3 | - | | | | |
| Reverse recovery charge | Q _{rr} | T _J = 25 °C | | - | 60 | - | nC | | | |
| | | T _J = 125 °C | | - | 210 | - | | | | |

| THERMAL - MECHANICAL SPECIFICATIONS | | | | | | | | | | |
|--|-----------------------------------|---|--------------|------|------------|------------------------|--|--|--|--|
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNITS | | | | |
| Maximum junction and storage temperature range | T _J , T _{Stg} | | -55 | - | 175 | °C | | | | |
| Thermal resistance, junction to case | R _{thJC} | | - | 1.8 | 2.0 | | | | | |
| Thermal resistance, junction to ambient | R _{thJA} | Typical socket mount | - | 50 | °C/W | | | | | |
| Thermal resistance, case to heatsink | R _{thCS} | Mounting surface, flat, smooth, and greased | - | 0.5 | - | | | | | |
| Waiaht | | | - | 2.0 | - | g | | | | |
| Weight | | | - | 0.07 | - | oz. | | | | |
| Mounting torque | | | 6.0 (5.0) | - | 12 (10) | kgf · cm (lbf · in) | | | | |
| Marking davias | | Case style D ² PAK (TO-263AB) | 8ETU04SH | | | | | | | |
| Marking device | | Case style TO-262 | | 8ETU | 04-1H | | | | | |

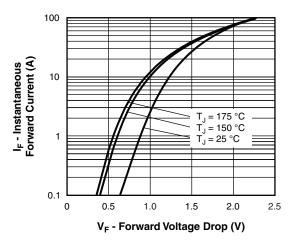


Fig. 1 - Typical Forward Voltage Drop Characteristics

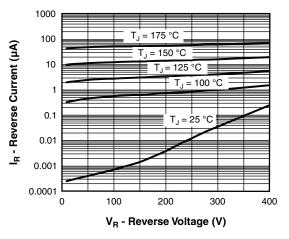


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage



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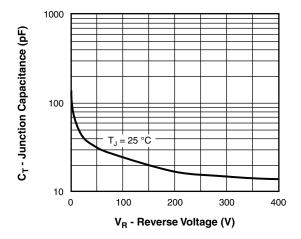


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

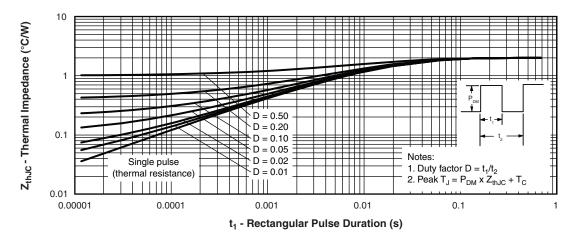
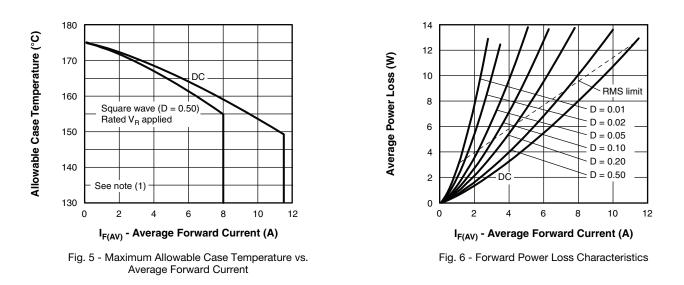


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics



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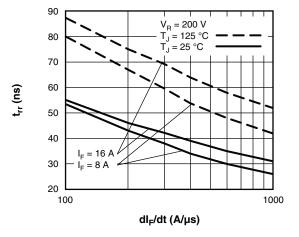


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

Note

- ⁽¹⁾ Formula used: $T_C = T_J (Pd + Pd_{REV}) \times R_{thJC}$;
- Pd = forward power loss = $I_{F(AV)} \times V_{FM}$ at $(I_{F(AV)}/D)$ (see fig. 6); Pd_{REV} = inverse power loss = $V_{R1} \times I_R$ (1 - D); I_R at V_{R1} = rated V_R

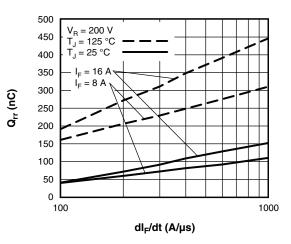


Fig. 8 - Typical Stored Charge vs. dl_F/dt

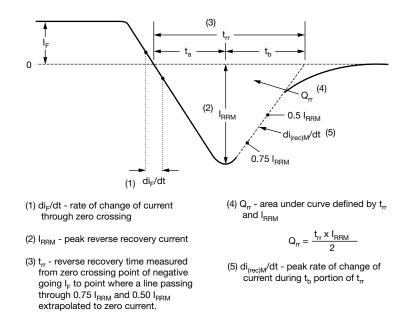
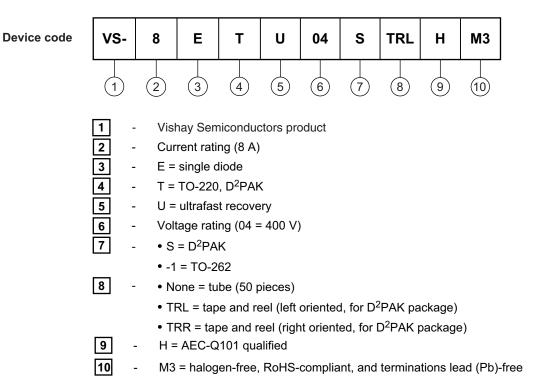


Fig. 9 - Reverse Recovery Waveform and Definitions



Vishay Semiconductors

ORDERING INFORMATION TABLE



| ORDERING INFORMATION (Example) | | | | | | | | |
|--------------------------------|---------------|--------------------------|--|--|--|--|--|--|
| PREFERRED P/N | BASE QUANTITY | PACKAGING DESCRIPTION | | | | | | |
| VS-8ETU04SHM3 | 50 | Antistatic plastic tube | | | | | | |
| VS-8ETU04STRRHM3 | 800 | 13"diameter reel | | | | | | |
| VS-8ETU04STRLHM3 | 800 | 13"diameter plastic reel | | | | | | |
| VS-8ETU04-1HM3 | 50 | Antistatic plastic tube | | | | | | |

| LINKS TO RELATED DOCUMENTS | | | | | | | | |
|----------------------------|-------------------------------|--------------------------|--|--|--|--|--|--|
| Dimensions | D ² PAK (TO-263AB) | www.vishay.com/doc?95046 | | | | | | |
| Dimensions | TO-262AA | www.vishay.com/doc?95419 | | | | | | |
| Deut escalia a information | D ² PAK (TO-263AB) | www.vishay.com/doc?95444 | | | | | | |
| Part marking information | TO-262AA | www.vishay.com/doc?95443 | | | | | | |
| Packaging information | D ² PAK (TO-263AB) | www.vishay.com/doc?95032 | | | | | | |

Outline Dimensions



D²PAK

DIMENSIONS in millimeters and inches

www.vishay.com

SHA



| SYMBOL | MILLIMETERS | | INCHES | | NOTES | NOTES | SYMBOL | MILLIM | IETERS | INC | HES | NOTES |
|--------|-------------|-------|--------|-------|-------|-------|--------|--------|--------|-------|-------|-------|
| STMBOL | MIN. | MAX. | MIN. | MAX. | NOTES | NOTES | STWDUL | MIN. | MAX. | MIN. | MAX. | NOTES |
| A | 4.06 | 4.83 | 0.160 | 0.190 | | | D1 | 6.86 | 8.00 | 0.270 | 0.315 | 3 |
| A1 | 0.00 | 0.254 | 0.000 | 0.010 | | | E | 9.65 | 10.67 | 0.380 | 0.420 | 2, 3 |
| b | 0.51 | 0.99 | 0.020 | 0.039 | | | E1 | 7.90 | 8.80 | 0.311 | 0.346 | 3 |
| b1 | 0.51 | 0.89 | 0.020 | 0.035 | 4 | | е | 2.54 | BSC | 0.100 | BSC | |
| b2 | 1.14 | 1.78 | 0.045 | 0.070 | | | Н | 14.61 | 15.88 | 0.575 | 0.625 | |
| b3 | 1.14 | 1.73 | 0.045 | 0.068 | 4 | | L | 1.78 | 2.79 | 0.070 | 0.110 | |
| С | 0.38 | 0.74 | 0.015 | 0.029 | | | L1 | - | 1.65 | - | 0.066 | 3 |
| c1 | 0.38 | 0.58 | 0.015 | 0.023 | 4 | | L2 | 1.27 | 1.78 | 0.050 | 0.070 | |
| c2 | 1.14 | 1.65 | 0.045 | 0.065 | | | L3 | 0.25 | BSC | 0.010 | BSC | |
| D | 8.51 | 9.65 | 0.335 | 0.380 | 2 | | L4 | 4.78 | 5.28 | 0.188 | 0.208 | |

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5 M-1994

⁽²⁾ Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

⁽³⁾ Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

⁽⁵⁾ Datum A and B to be determined at datum plane H

⁽⁶⁾ Controlling dimension: inch

⁽⁷⁾ Outline conforms to JEDEC[®] outline TO-263AB

Revision: 08-Jul-15

1

Outline Dimensions



Vishay Semiconductors

TO-262

DIMENSIONS in millimeters and inches



Lead tip -



E1 Plating



Е

MILLIMETERS INCHES SYMBOL NOTES MIN. MAX. MIN. MAX. А 4.06 4.83 0.160 0.190 2.03 A1 3.02 0.080 0.119 b 0.51 0.99 0.020 0.039 b1 0.51 0.89 0.020 0.035 4 b2 1.14 1.78 0.045 0.070 1.14 1.73 0.045 0.068 4 b3 0.38 0.74 0.015 0.029 С 0.38 0.58 0.015 0.023 4 c1 1.14 1.65 0.045 0.065 c2 D 8.51 9.65 0.335 0.380 2 D1 6.86 8.00 0.270 0.315 3 Е 9.65 10.67 0.380 0.420 2, 3 E1 7.90 8.80 0.311 0.346 3 0.100 BSC 2.54 BSC е L 13.46 14.10 0.530 0.555 L1 _ 1.65 0.065 3 _ 3.36 0.132 0.146 L2 3.71

3. - Anode

Notes

⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

(5) Controlling dimension: inches

⁽²⁾ Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

⁽³⁾ Thermal pad contour optional within dimension E, L1, D1 and E1

Outline conform to JEDEC TO-262 except A1 (maximum), (6) b (minimum), D1 (minimum) and L2 where dimensions derived the actual package outline

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Document Number: 95419

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